

C3
33. (amended) The photoresist composition of claim 26 wherein prior to reaction with the polymer the crosslinker component is a vinyl ether.

34. (amended) The photoresist composition of claim 26 wherein prior to reaction with the polymer the crosslinker component is 1,4-butanedivinyl ether, 1,6-hexanedinyether, 1,4-cyclohexane dimethanoldivinyl ether or bis-vinylether ethane ether.

Sub 32
35. (amended) A method for forming a photoresist relief image, comprising:
a) applying a layer of a positive-acting photoresist composition on a substrate, the photoresist composition comprising a photoactive component and a polymer that is substantially free of aromatic groups and comprises 1) units crosslinked to other polymer units and 2) photoacid-labile groups, the polymer units being crosslinked by a separate crosslinker component; and
b) exposing and developing the photoresist layer on the substrate to yield a photoresist relief image.

41. (amended) The method of claim 35 wherein the photoacid-labile groups comprise acrylate esters that comprise a tertiary non-cyclic group or a secondary or tertiary alicyclic group.

Remarks

Applicant appreciates the indication of allowable subject matter, i.e. that claims 31-35 would be allowable if rewritten in independent form.

The pending independent claims 26 and 35 have been amended herein to recite features that were indicated to be allowable.